



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Application of :
Hirofumi HARADA :
Serial No. 09/872,798 : Group Art Unit: 2814
Filed: June 1, 2001 : Examiner: Thao X. Le
For: VERTICAL MOS TRANSISTOR
AND A METHOD OF
MANUFACTURING THE SAME : Docket No. S004-4310(RCE)

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COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, DC 20231

AMENDMENT UNDER 37 CFR §1.114

S I R:

In response to the final Office Action dated November 29, 2002, applicant amends his application as follows:

IN THE SPECIFICATION:

Replace the paragraph beginning 4 lines from the bottom of page 8 with the following rewritten paragraph:

--Fig. 1 is a sectional view of an N channel vertical MOS transistor according to the present invention. A